

1 / 14

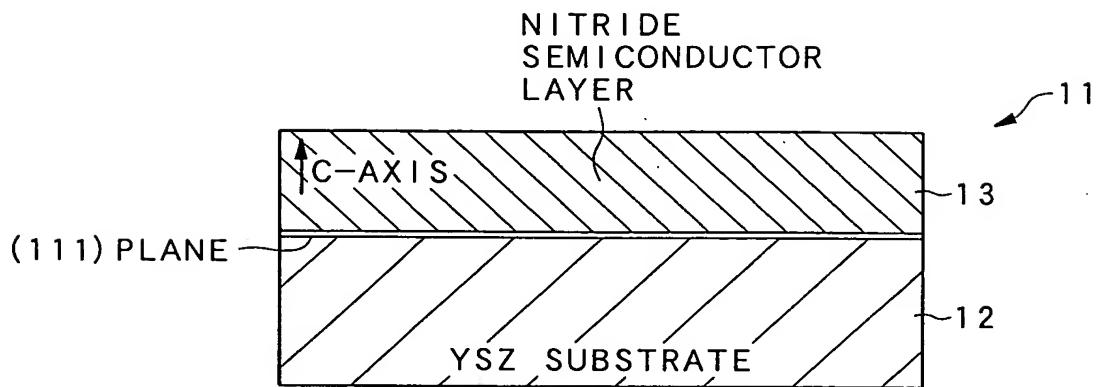


FIG. 1

2 / 14

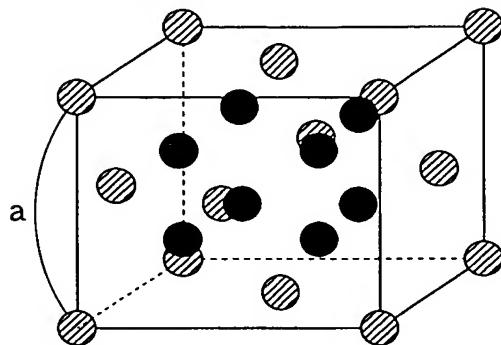


FIG. 2A

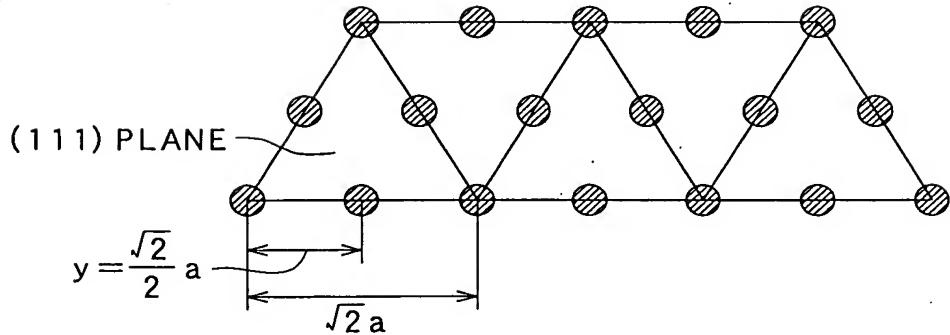


FIG. 2B

3 / 14

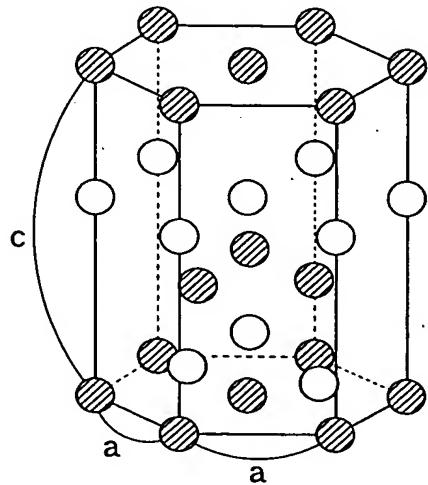


FIG. 3 A

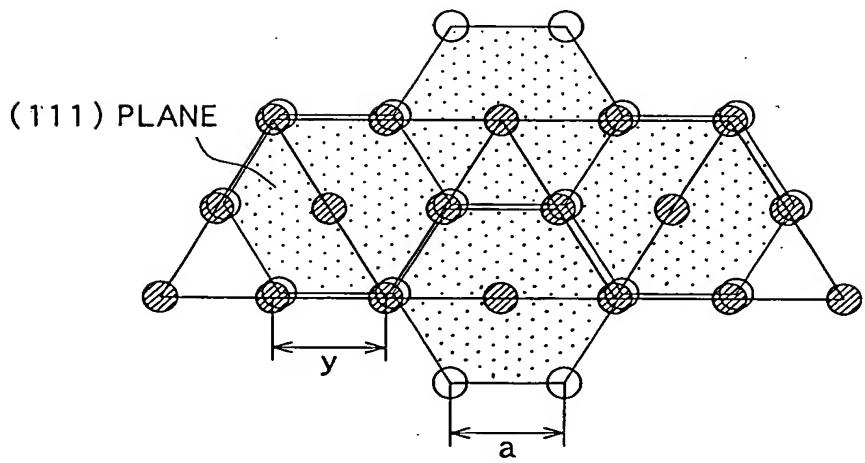


FIG. 3 B

4 / 14

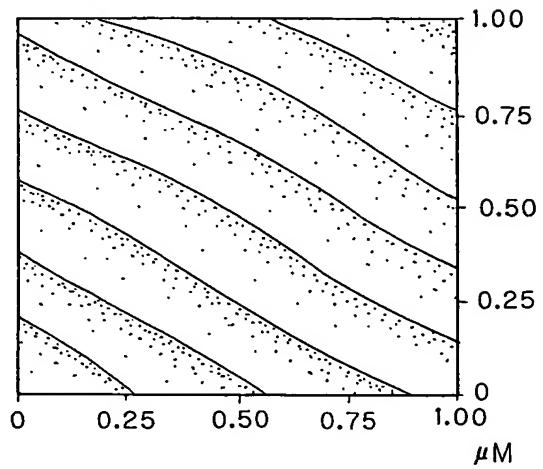


FIG. 4

5 / 14

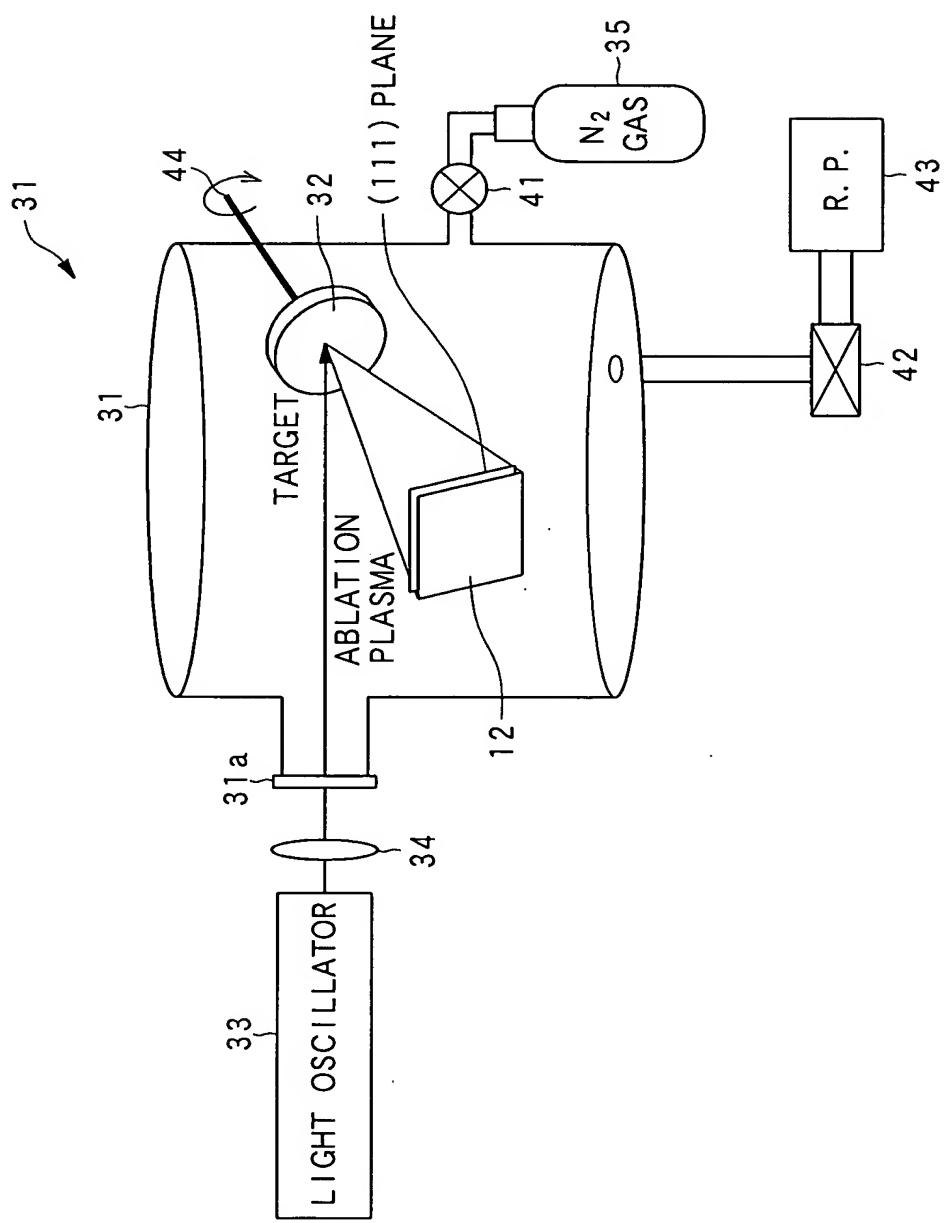


FIG. 5

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6 / 14

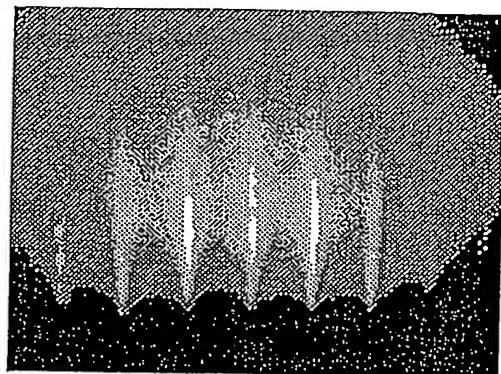


FIG. 6

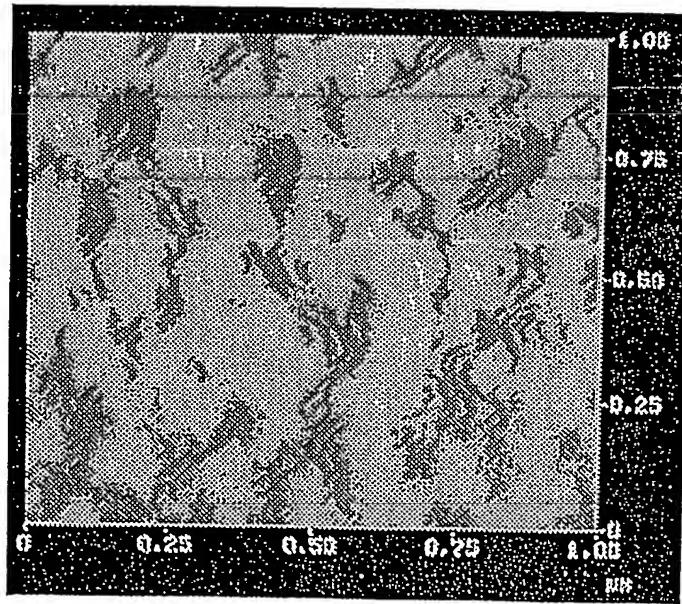


FIG. 7

7 / 14

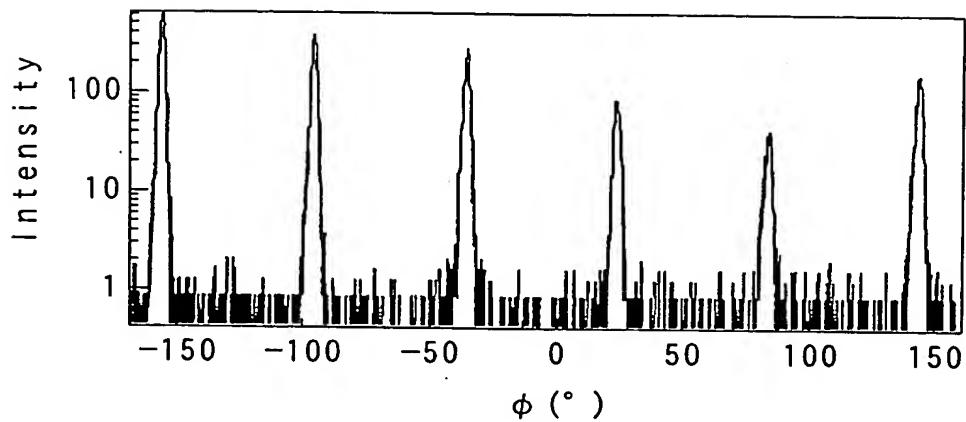


FIG. 8A

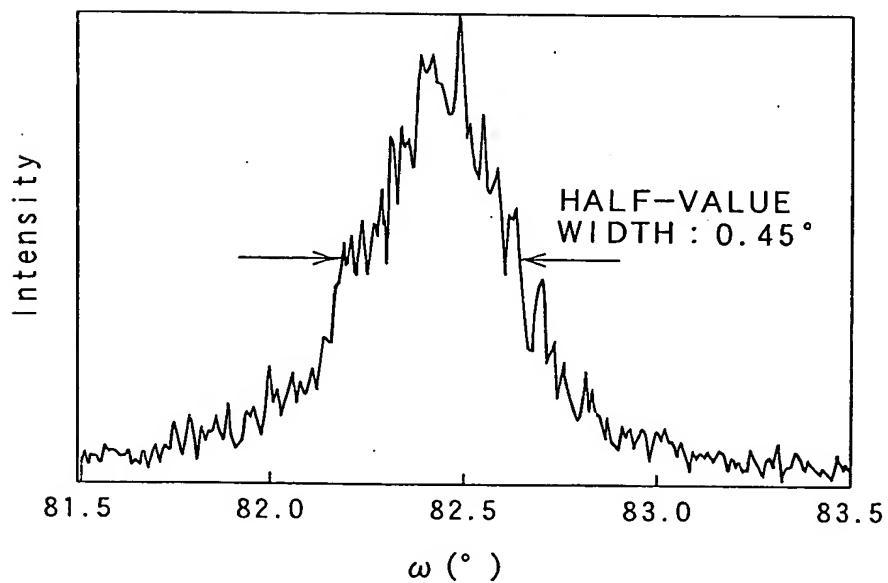


FIG. 8B

8 / 14

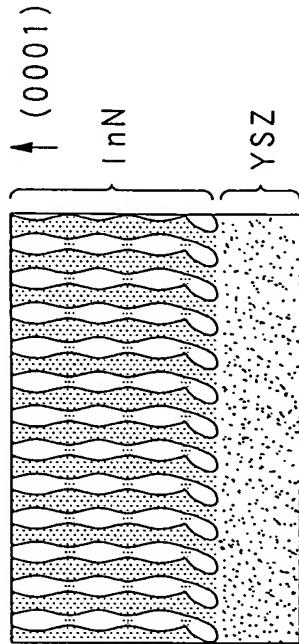


FIG. 9B

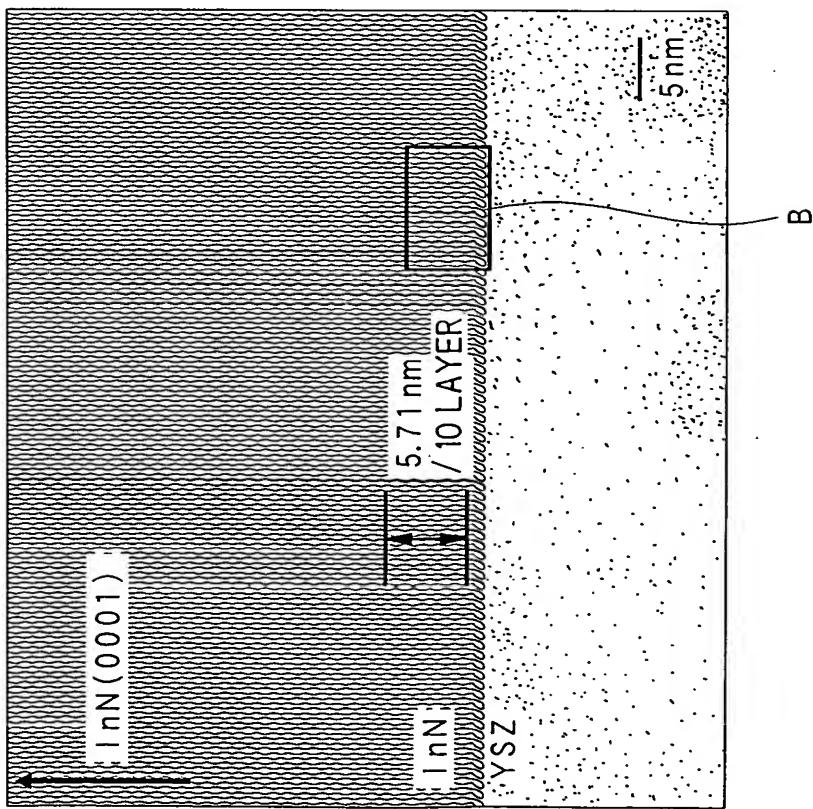


FIG. 9A

9 / 14

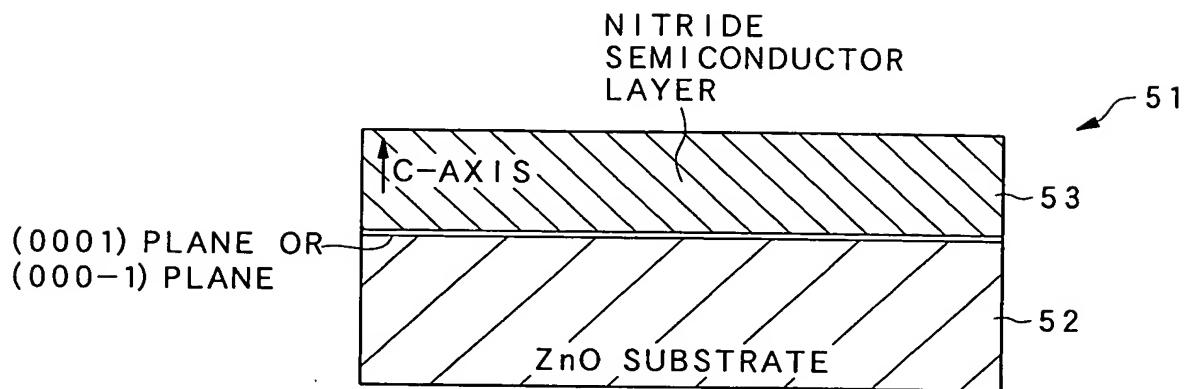


FIG.10

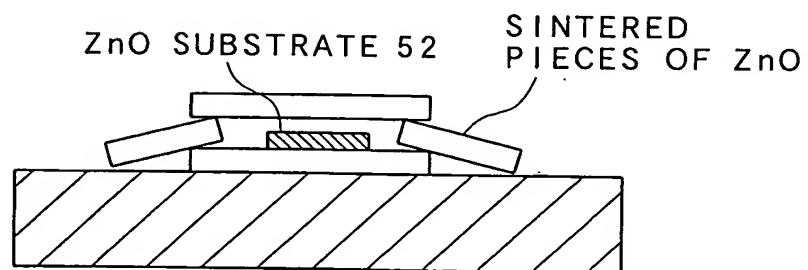
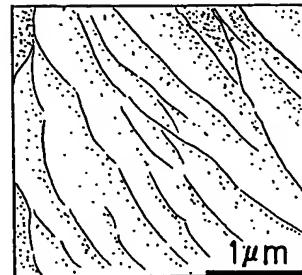


FIG.11

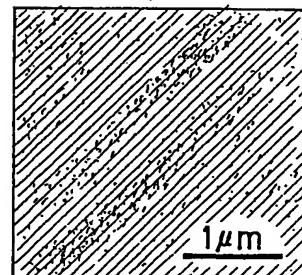
10/14

FIG.12A



1150 °C 6.5h

FIG.12B



1150 °C 3.5h

11 / 14

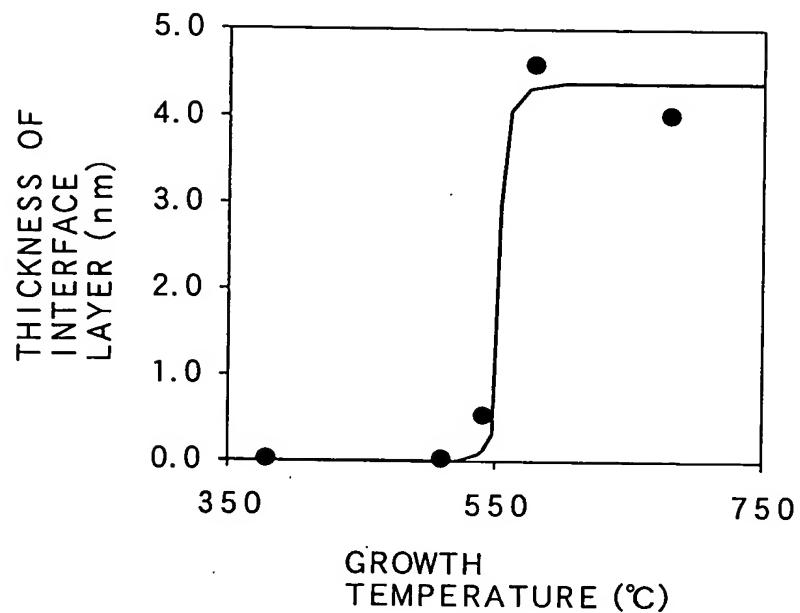


FIG. 13

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Inventor(s): Fujioka et al.
NITRIDE SEMICONDUCTOR DEVICE AND METHOD FOR
PREPARATION THEREOF
Filed January 6, 2006; Atty. Docket No. 113184-114

12 / 14

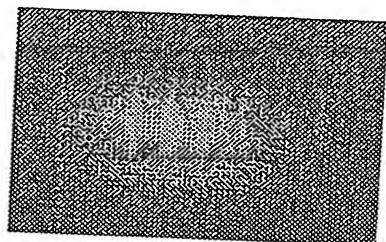


FIG. 14 A

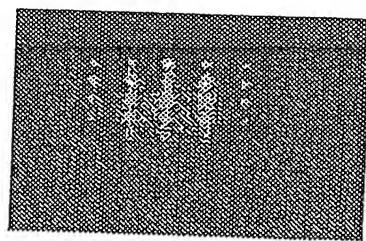


FIG. 14 B

13 / 14

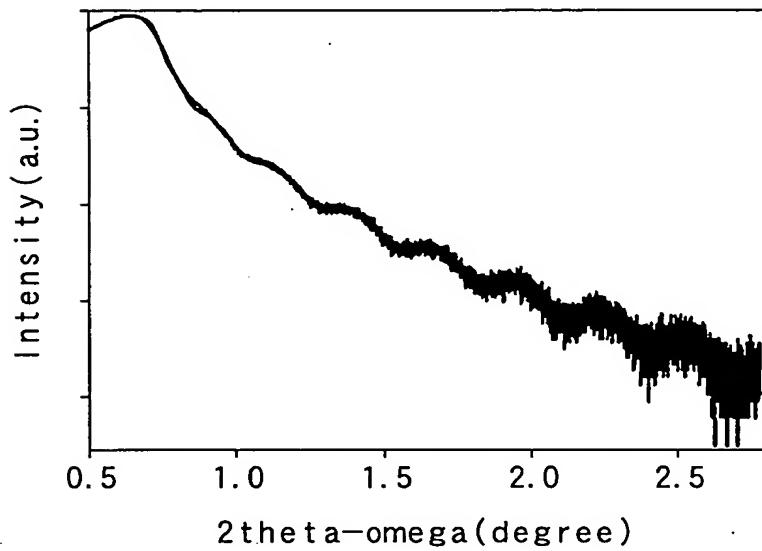


FIG.15

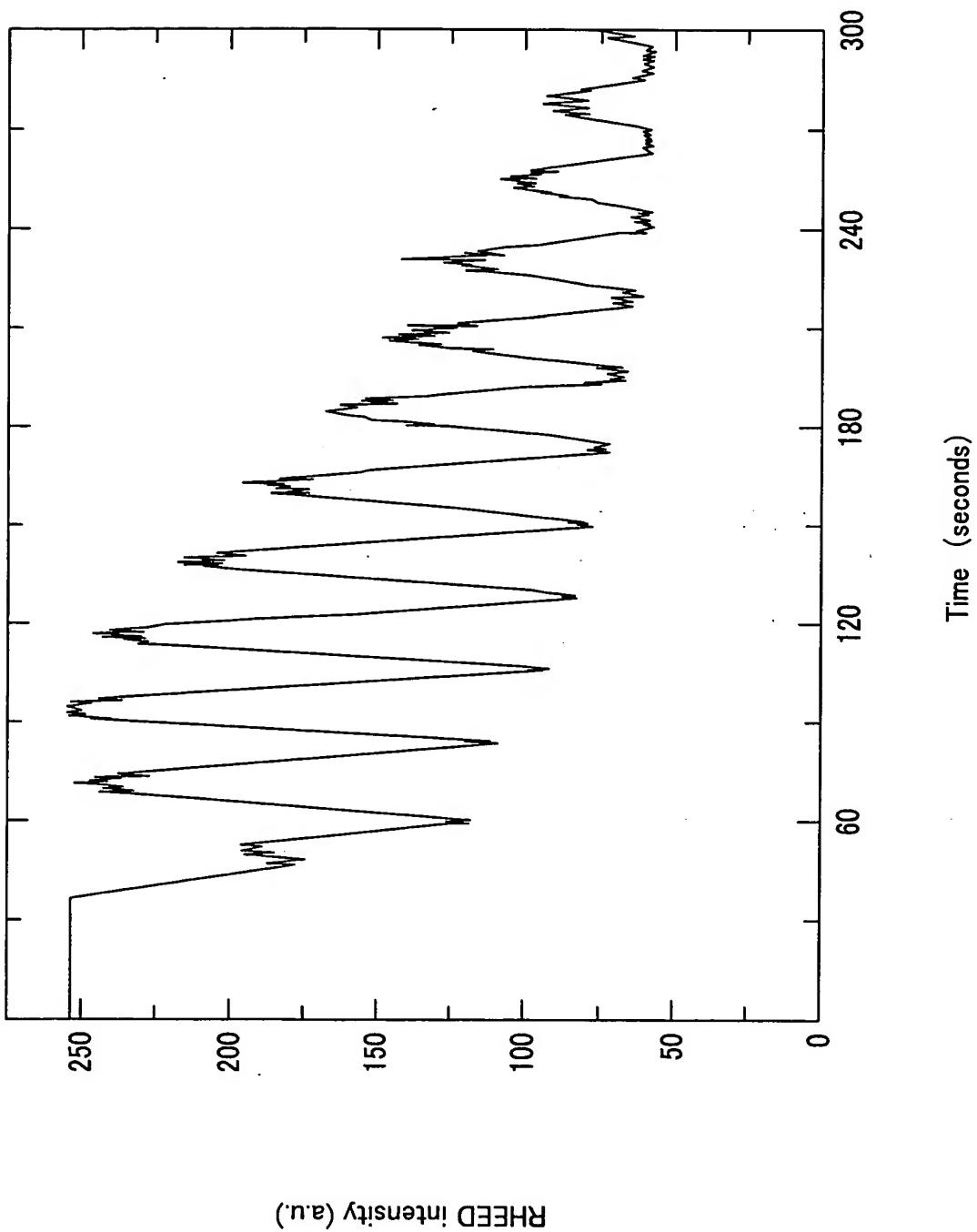


FIG. 16